Amendments to the Abstract:

Kindly amend the Abstract on page 28 as indicated below.

A process for producing a doped silicon single crystal, ~~which is doped with highly volatile foreign substance by pulling the single crystal from a melt which is held under predetermined process conditions in a crucible. A quantity of the foreign substance N_0 is added in order to achieve a desired resistance of the melt, and the melt, after a time t, is after-doped at least once with a quantity $\Delta N(t)$ of the foreign substance, in order to compensate for losses caused by the foreign substance evaporating out of the melt. The quantity $\Delta N(t)$ of the foreign substance~~ comprising after-doping the melt during the pulling process with a quantity of volatile dopant $\Delta N(t)$, calculated according to the equation

$$\Delta N(t) = N_0 - N(t) = N_0 \cdot (1 - e^{-\lambda a \cdot t})$$

or according to the approximation equation

$$\Delta N(t) = N_0 \cdot \lambda_a \cdot t$$

where λ_a is an evaporation coefficient which describes [[a]] process-specific evaporation behavior of the foreign substance and which is obtained after a resistance profile R(t) of a further single crystal has been measured and ~~by calculation~~ calculated according to the equation

$$R(t) = R_0 \cdot e^{\lambda a \cdot t} ,$$

where R_0 is a starting resistivity and the further single crystal is pulled under the ~~predetermined~~ same process conditions without being after-doped with the foreign substance.